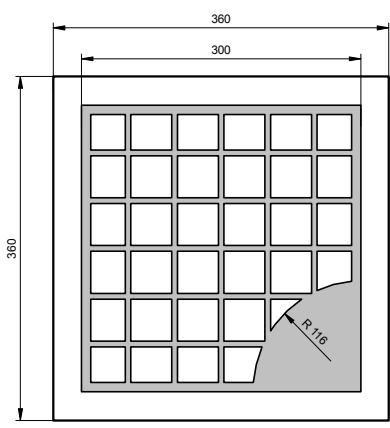


Radiation	Type	Technology	Electrodes
Infrared	MQW	InGaAs/InP	P (anode) up

 <p style="text-align: center;">LED-11</p>	typ. dimensions (μm)	
	<u>typ. thickness</u> 260 μm <u>anode</u> gold alloy, 1.5 μm <u>cathode</u> gold alloy, 0.5 μm	

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I _F			100	mA
Peak forward current	t _p ≤ 50 μs, t _p /T = 1/2	I _{FM}			200	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		1.05	1.3	V
Forward voltage	I _F = 100 mA	V _F		1.20	1.4	V
Reverse voltage	I _R = 100 μA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	0.4	0.6		mW
Radiant power ¹	I _F = 100 mA	Φ _e	2.0	2.8		mW
Radiant power ²	I _F = 100 mA	Φ _e		5.5		mW
Peak wavelength	I _F = 100 mA	λ _p	1040	1060	1080	nm
Spectral bandwidth at 50%	I _F = 100 mA	Δλ _{0.5}		50		nm
Switching time	I _F = 100 mA	t _r , t _f		10		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-1060-17				

Packing: Chips on adhesive film with wire-bond side on top